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Photomask Technology 2022

Bryan S. Kasprowicz
Editor

26–29 September 2022
Monterey, California, United States

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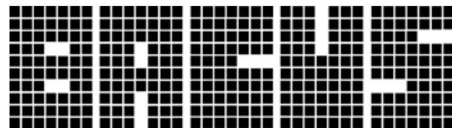

The international technical group of SPIE dedicated
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SPIE

Volume 12293

Proceedings of SPIE 0277-786X, V. 12293

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Photomask Technology 2022, edited by Bryan S. Kasprowicz, Proc. of SPIE Vol. 12293,
1229301 · © 2022 SPIE · 0277-786X · doi: 10.1117/12.2667057

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Author(s), "Title of Paper," in *Photomask Technology 2022*, edited by Bryan S. Kasprowicz, Proc. of SPIE 12293, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510656413
ISBN: 9781510656420 (electronic)

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time)
SPIE.org
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Contents

vii *Conference Committee*

INSPECTION/REPAIR

12293 06 **Mask inspection technologies for expanding EUV lithography (Invited Paper)** [12293-7]

12293 07 **Introduction of new visual analysis program using defect image segmentation for EUV mask mass product at modern load port** [12293-8]

12293 08 **AFM clean and nanomachining repair technology for future mask nodes** [12293-9]

12293 0A **Towards improving challenging stochastic defect detection in SEM images based on improved YOLOv5** [12293-11]

CURVILINEAR MASKS

12293 0C **A study of ILT-based curvilinear SRAF with a constant width** [12293-2]

12293 0D **You don't need 1nm contours for curvilinear shapes: pixel-based computing is the answer** [12293-3]

12293 0E **Assessment of contour modeling readiness for curvilinear masks** [12293-4]

12293 0F **A method for calibrating a curvature-based pre-bias model for advanced mask process correction applications** [12293-5]

ADVANCED CLEANING

12293 0H **In-situ cavitation measurements with a wireless sensor array: applications in megasonic photomask cleaning** [12293-18]

12293 0I **Removal behavior of Sn and Pb contaminants on EUV mask after EUV exposure** [12293-19]

PSM MASK: JOINT SESSION WITH PHOTOMASK AND EUV CONFERENCES

12293 0M **A study of patterning 36nm-pitch logic contact holes in a metal oxide resist using a high-reflectance phase-shifting mask that results in image reversal** [12293-23]

RESIST MATERIALS AND PROCESS I: JOINT SESSION WITH PHOTOMASK AND EUV CONFERENCES

12293 0N **Robust and reliable actinic ptychographic imaging of highly periodic structures in EUV photomasks** [12293-50]

ALTERNATIVE APPLICATIONS

12293 0P **Nanoimprint performance improvements for high volume semiconductor device manufacturing** [12293-13]

12293 0Q **Characteristics of fine feature hole templates for nanoimprint lithography toward 2nm and beyond** [12293-14]

MASK PROCESS CORRECTION

12293 0U **Benefits of SEM field-of-view contour averaging for contour-based MPC modeling** [12293-24]

12293 0V **A neural network assisted etch model for mask process correction** [12293-26]

12293 0W **Mask process correction for laser writers** [12293-27]

MASK METROLOGY

12293 0Z **Investigation of stochastic roughness effects for nanoscale grating characterization with a stand-alone EUV spectrometer** [12293-30]

12293 10 **Direct correlation between mask registration and on-wafer measurements for individual logic device features** [12293-31]

12293 12 **Extreme ultraviolet lithography reticle local CD uniformity correlation to wafer local CD uniformity** [12293-33]

WRITE AND PROCESS

12293 14 **Study of EB resist dissolution contrast and chemical blur impact on the ultimate resolution** [12293-34]

12293 17 **Multibeam mask requirements for advanced EUV patterning** [12293-38]

POSTER SESSION

12293 19 **Bayesian optimization-based estimation of effective reaction radius of chemically amplified resist in acid catalyzed deprotection reaction** [12293-39]

12293 1A **Single-pass frame generation for multi-layer 3D circuits** [12293-40]

12293 1C **Aerial image metrology (AIMS) based mask-model accuracy improvement for computational lithography** [12293-42]

12293 1D **The feasibility of alternative blank substrate materials for large-scale FPD mask process and manufacturing** [12293-43]

12293 1E **A study of rare contamination defects come in a vacuum chamber** [12293-44]

12293 1F **Data preparation for digital scanner** [12293-45]

12293 1G **Depth of focus in high-NA EUV lithography: a simulation study** [12293-46]

12293 1H **Haze classification based on location for COG mask** [12293-49]

12293 1J **Research of high-transmission phase-shift mask on critical dimension uniformity in ArF lithography** [12293-52]

12293 1K **Precise optical constants: determination and impact on metrology, simulation, and development of EUV masks** [12293-53]

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